

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Express Mail Number EV342470493US

Docket Number (Optional)

100-22900 (P05685)

Application Number

New

Applicant(s)

Vladislav Vashchenko et al.

Filing Date

Herewith

Group Art Unit

Unknown

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>W</i>		Pat. Appln. 10/649,989		Vladislav Vashchenko et al.			08/27/03
<i>W</i>		Pat. Appln. 10/650,000		Vladislav Vashchenko et al.			08/27/03
<i>W</i>		6,433,368 B1	08/13/02	Vladislav Vashchenko et al.	257	173	01/22/01

## FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>W</i>		G. Charitat, "Voltage Handling Capability and Termination Techniques of Silicon Power Semiconductor Devices", IEEE BCTM 11.1, 2001, pps. 175-183.
<i>W</i>		Julian Z. Chen, Ajith Amerasekera and Tom Vrotsos, "Bipolar SCR ESD Protection Circuit for High Speed Submicron Bipolar/BiCMOS Circuits", IEDM, pps. 337-340, (14.1 - 14.1.4), 1995, IEEE.

EXAMINER

*Kevin Quilty*

DATE CONSIDERED

*5/17/04*

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.